INTEGRATED CIRCUITS



Product specification Supersedes data of 1997 Feb 03 IC24 Data Handbook

1998 Apr 28



74LV126

FEATURES

- Wide operating voltage: 1.0 to 5.5 V
- Optimized for low voltage applications: 1.0 to 3.6 V
- Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- Typical V_{OLP} (output ground bounce) < 0.8 V at V_{CC} = 3.3 V, $T_{amb} = 25^{\circ}C$
- Typical V_{OHV} (output V_{OH} undershoot) > 2 V at V_{CC} = 3.3 V, $T_{amb} = 25^{\circ}C$
- · Output capability: bus driver
- I_{CC} category: MSI

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25^{\circ}C$; $t_r = t_f \le 2.5$ ns

DESCRIPTION

The 74LV126 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC/HCT126.

The 74LV126 consists of four non-inverting buffers/line drivers with 3-state outputs. The 3-state outputs (nY) are controlled by the output enable input (nOE). A LOW at nOE causes the outputs to assume a high impedance OFF-state.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t _{PHL} /t _{PLH}	Propagation delay nA to nY	C _L = 15 pF; V _{CC} = 3.3 V	9	ns
Cl	Input capacitance		3.5	pF
C _{PD}	Power dissipation capacitance per buffer	$V_{CC} = 3.3 \text{ V};$ V _I = GND to V _{CC} ¹	23	pF

NOTE:

 C_{PD} is used to determine the dynamic power dissipation (P_D in $\mu W)$ 1.

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} + \sum (C_{L} \times V_{CC}^{2} \times f_{0}) \text{ where:} \\f_{i} = \text{ input frequency in MHz; } C_{L} = \text{ output load capacitance in pF;} \\f_{0} = \text{ output frequency in MHz; } V_{CC} = \text{ supply voltage in V;}$

 $\sum (C_L \times V_{CC}^2 \times f_0) =$ sum of the outputs.

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	PKG. DWG. #
14-Pin Plastic DIL	–40°C to +125°C	74LV126 N	74LV126 N	SOT27-1
14-Pin Plastic SO	–40°C to +125°C	74LV126 D	74LV126 D	SOT108-1
14-Pin Plastic SSOP Type II	–40°C to +125°C	74LV126 DB	74LV126 DB	SOT337-1
14-Pin Plastic TSSOP Type I	–40°C to +125°C	74LV126 PW	74LV126PW DH	SOT402-1

PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
1, 4, 10, 13	10E – 40E	Output enable inputs (active HIGH)
2, 5, 9, 12	1A – 4A	Data inputs
3, 6, 8, 11	1Y – 4Y	Data outputs
7	GND	Ground (0 V)
14	V _{CC}	Positive supply voltage

FUNCTION TABLE

INP	JTS	OUTPUTS		
nOE	nA	nY		
н	L	L		
н	Н	Н		
L	Х	Z		

NOTES:

H = HIGH voltage level

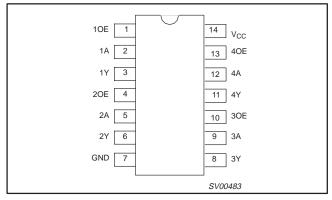
L = LOW voltage level

X = don't care

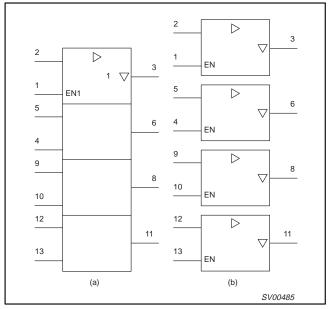
Z = high impedance OFF-state

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PIN CONFIGURATION



LOGIC SYMBOL (IEEE/IEC)



9

12 4A

13 4OE

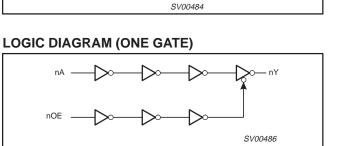
3A

10 3OE

3Y 8

4Y 11

LOGIC SYMBOL



RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{CC}	DC supply voltage	See Note 1	1.0	3.3	5.5	V
VI	Input voltage		0	-	V _{CC}	V
Vo	Output voltage		0	-	V _{CC}	V
T _{amb}	Operating ambient temperature range in free air	See DC and AC characteristics	-40 -40		+85 +125	°C
t _r , t _f	Input rise and fall times	$V_{CC} = 1.0V \text{ to } 2.0V \\ V_{CC} = 2.0V \text{ to } 2.7V \\ V_{CC} = 2.7V \text{ to } 3.6V \\ V_{CC} = 3.6V \text{ to } 5.5V$	- - - -	- - -	500 200 100 50	ns/V

NOTE:

1. The LV is guaranteed to function down to V_{CC} = 1.0V (input levels GND or V_{CC}); DC characteristics are guaranteed from V_{CC} = 1.2V to V_{CC} = 5.5V.

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ABSOLUTE MAXIMUM RATINGS^{1, 2}

In accordance with the Absolute Maximum Rating System (IEC 134). Voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
$\pm I_{IK}$	DC input diode current	$V_{\rm I} < -0.5 \text{ or } V_{\rm I} > V_{\rm CC} + 0.5 V$	20	mA
$\pm I_{OK}$	DC output diode current	$V_{\rm O}$ < -0.5 or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5V	50	mA
$\pm I_{O}$	DC output source or sink current – bus driver outputs	35	mA	
$^{\pm I}_{GND}, \\ ^{\pm I}_{CC}$	DC V _{CC} or GND current for types with – bus driver outputs		70	mA
T _{stg}	Storage temperature range		–65 to +150	°C
P _{TOT}	Power dissipation per package – plastic DIL – plastic mini-pack (SO) – plastic shrink mini-pack (SSOP and TSSOP)	for temperature range: -40 to +125°C above +70°C derate linearly with 12 mW/K above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	750 500 400	mW

NOTES:

1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions, voltages are referenced to GND (ground = 0 V)

					LIMITS				
SYMBOL	PARAMETER	TEST CONDITIONS	-40	°C to +8	5°C	-40°C to	o +125°C	UNIT	
			MIN	TYP ¹	MAX	MIN	MAX	1	
		V _{CC} = 1.2 V	0.9			0.9			
V	HIGH level Input	V _{CC} = 2.0 V	1.4			1.4		v	
VIH	voltage	$V_{CC} = 2.7 \text{ to } 3.6 \text{ V}$	2.0			2.0			
		$V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$	0.7 * V _{CC}			0.7 * V _{CC}		1	
V _{IL} LOW level Input voltage	V _{CC} = 1.2 V			0.3		0.3			
	V _{CC} = 2.0 V			0.6		0.6	v		
	V _{CC} = 2.7 to 3.6 V			0.8		0.8			
		V _{CC} = 4.5 to 5.5			0.3 * V _{CC}		0.3 * V _{CC}	1	
		$V_{CC} = 1.2 \text{ V}; \text{ V}_{I} = \text{V}_{IH} \text{ or } \text{V}_{IL}; -\text{I}_{O} = 100 \mu\text{A}$		1.2					
		$V_{CC} = 2.0 \text{ V}; \text{ V}_{I} = \text{V}_{IH} \text{ or } \text{V}_{IL}; -\text{I}_{O} = 100 \mu\text{A}$	1.8	2.0		1.8		v	
V _{OH}	HIGH level output voltage; all outputs	$V_{CC} = 2.7 \text{ V}; \text{ V}_{I} = \text{V}_{IH} \text{ or } \text{V}_{IL}; -\text{I}_{O} = 100 \mu\text{A}$	2.5	2.7		2.5			
		$V_{CC} = 3.0 \text{ V}; \text{ V}_{I} = \text{V}_{IH} \text{ or } \text{V}_{IL;} - \text{I}_{O} = 100 \mu \text{A}$	2.8	3.0		2.8			
		V_{CC} = 4.5 V; V_I = V_{IH} or V_{IL} ; $-I_O$ = 100 μ A	4.3	4.5		4.3			
M	HIGH level output voltage; BUS driver	V_{CC} = 3.0 V; V_{I} = V_{IH} or $V_{IL;}$ – I_{O} = 8mA	2.40	2.82		2.20		v	
V _{OH}	outputs	$V_{CC} = 4.5 \text{ V}; \text{ V}_{I} = \text{V}_{IH} \text{ or } \text{V}_{IL;} - \text{I}_{O} = 16\text{mA}$	3.60	4.20		3.50			
		$V_{CC} = 1.2 \text{ V}; \text{ V}_{I} = \text{V}_{IH} \text{ or } \text{V}_{IL}; \text{ I}_{O} = 100 \mu \text{A}$		0					
		$V_{CC} = 2.0 \text{ V}; \text{ V}_{I} = \text{V}_{IH} \text{ or } \text{V}_{IL}; \text{ I}_{O} = 100 \mu \text{A}$		0	0.2		0.2	1	
V _{OL}	LOW level output voltage; all outputs	V_{CC} = 2.7 V; V_I = V_{IH} or V_{IL} ; I_O = 100 μ A		0	0.2		0.2	V	
	i sinago, an outputo	V_{CC} = 3.0 V; V_I = V_{IH} or V_{IL} ; I_O = 100 μ A		0	0.2		0.2		
		$V_{CC} = 4.5 \text{ V}; \text{ V}_{I} = \text{V}_{IH} \text{ or } \text{V}_{IL}; \text{ I}_{O} = 100 \mu \text{A}$		0	0.2		0.2	1	

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DC ELECTRICAL CHARACTERISTICS (Continued)

Over recommended operating conditions, voltages are referenced to GND (ground = 0 V)

					LIMITS			
SYMBOL	PARAMETER	TEST CONDITIONS	-40)°C to +8	5°C	-40°C to	UNIT	
			MIN	TYP ¹	MAX	MIN	MAX	
LOW level output voltage; BUS driver		V_{CC} = 3.0 V; V_{I} = V_{IH} or $V_{IL;}I_{O}$ = 8mA		0.20	0.40		0.50	V
V _{OL} voltage; BUS driver outputs	V_{CC} = 4.5 V; V_{I} = V_{IH} or $V_{IL;}$ I_{O} = 16mA		0.35	0.55		0.65	v	
I	Input leakage current	V_{CC} = 5.5 V; V_{I} = V_{CC} or GND			1.0		1.0	μΑ
I _{OZ}	3-State output OFF-state current	$V_{CC} = 5.5 \text{ V}; V_I = V_{IH} \text{ or } V_{IL};$ $V_O = V_{CC} \text{ or GND}$			5		10	μΑ
Icc	Quiescent supply current; MSI	V_{CC} = 5.5 V; V_{I} = V_{CC} or GND; I_{O} = 0			20.0		160	μΑ
ΔI _{CC}	Additional quiescent supply current per input	V_{CC} = 2.7 V to 3.6 V; V_{I} = V_{CC} – 0.6 V			500		850	μΑ

NOTE:

1. All typical values are measured at $T_{amb} = 25^{\circ}C$.

AC CHARACTERISTICS

 $GND = 0V; \ t_{f} = t_{f} \leq 2.5 ns; \ C_{L} = 50 pF; \ R_{L} = 500 \Omega$

			CONDITION			LIMITS				
SYMBOL	PARAMETER	WAVEFORM	CONDITION	_	40 to +85	°C	–40 to +125 °C		UNIT	
			V _{CC} (V)	MIN	TYP ¹	MAX	MIN	MAX		
			1.2		55					
			2.0		19	24		31		
t _{PHL} /t _{PLH} Propagation delay nA to nY	Figures 1, 2	2.7		14	18		23	ns		
		3.0 to 3.6		10 ²	14		18			
			4.5 to 5.5			12		15		
			1.2		75					
	3-state output		2.0		26	31		39	ns	
t _{PZH} /t _{PZL}	enable time	Figures 1, 2	2.7		19	23		29		
	nOE to nY		3.0 to 3.6		14 ²	18		23		
			4.5 to 5.5			15		19		
			1.2		65					
	3-state output		2.0		24	32		39		
t _{PHZ} /t _{PLZ}	disable time	Figures 1, 2	2.7		28	24		29	ns	
	nOE to nY		3.0 to 3.6		14 ²	20		24		
			4.5 to 5.5			17		21	1	

NOTES:

1. Unless otherwise stated, all typical values are measured at $T_{amb} = 25^{\circ}C$ 2. Typical values are measured at $V_{CC} = 3.3 \text{ V}$.

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AC WAVEFORMS

 $V_M = 1.5 \text{ V at } V_{CC} \ge 2.7 \text{ V and } \le 3.6 \text{ V};$ $V_M = 0.5 \times V_{CC} \text{ at } V_{CC} < 2.7 \text{ V and } \ge 4.5 \text{ V};$ V_{OL} and V_{OH} are the typical output voltage drop that occur with the output load.

 $\begin{array}{l} {\sf V}_X = {\sf V}_{OL} + 0.3 \; {\sf V} \; at \; {\sf V}_{CC} \geq 2.7 \; {\sf V} \; and \leq 3.6 \; {\sf V}; \\ {\sf V}_X = {\sf V}_{OL} + 0.1 \times {\sf V}_{CC} \; at \; {\sf V}_{CC} < 2.7 \; {\sf V} \; and \geq 4.5 \; {\sf V}. \\ {\sf V}_Y = {\sf V}_{OH} - 0.3 \; {\sf V} \; at \; {\sf V}_{CC} \geq 2.7 \; {\sf V} \; and \leq 3.6 \; {\sf V}; \\ {\sf V}_Y = {\sf V}_{OH} - 0.1 \times {\sf V}_{CC} \; at \; {\sf V}_{CC} < 2.7 \; {\sf V} \; and \geq 4.5 \; {\sf V}. \end{array}$

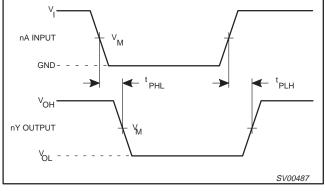


Figure 1. Input (nA, nB) to output (nY) propagation delays

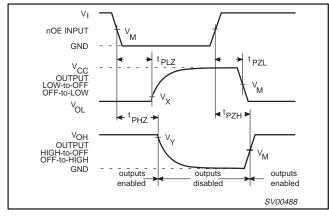


Figure 2. 3-state enable and disable times.

TEST CIRCUIT

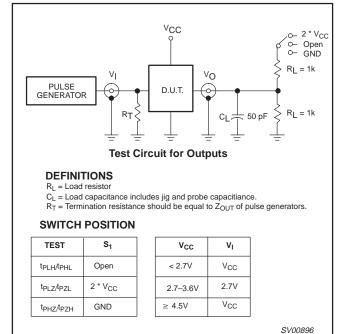
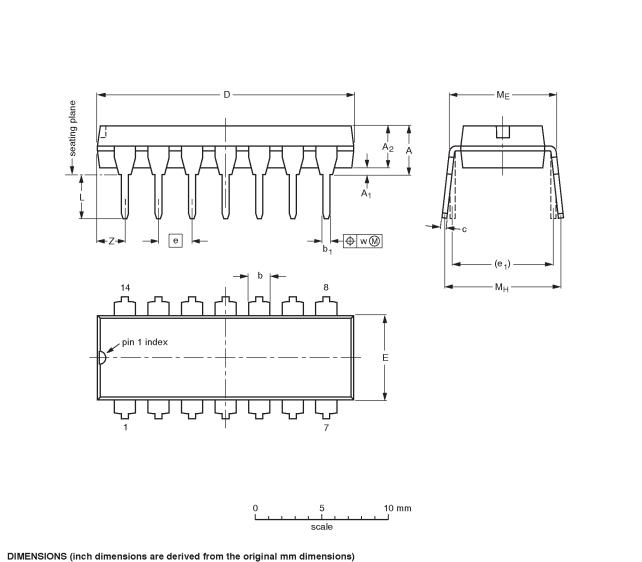


Figure 3. Load circuitry for switching times.





UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

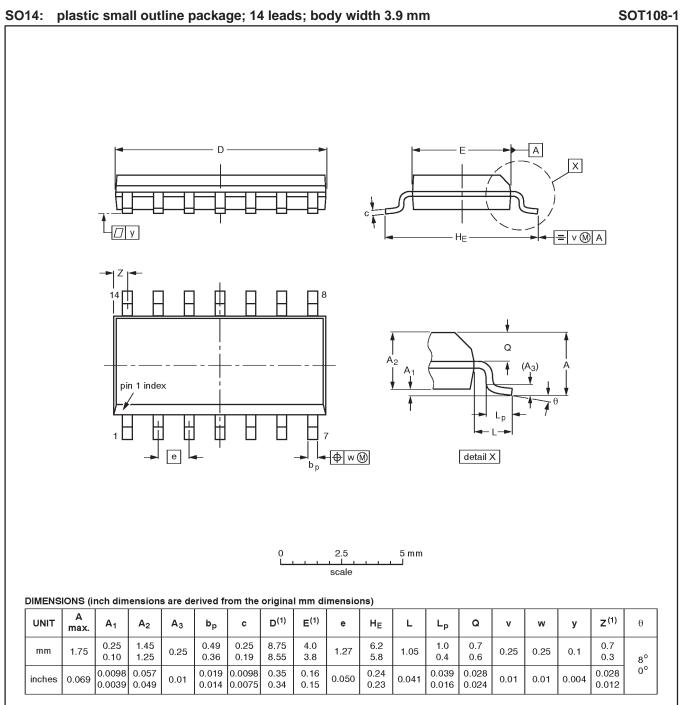
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION		REFER	EUROPEAN	ISSUE DATE		
	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT27-1	050G04	MO-001AA				-92-11-17 95-03-11

Product specification 74LV126

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Product specification



Note

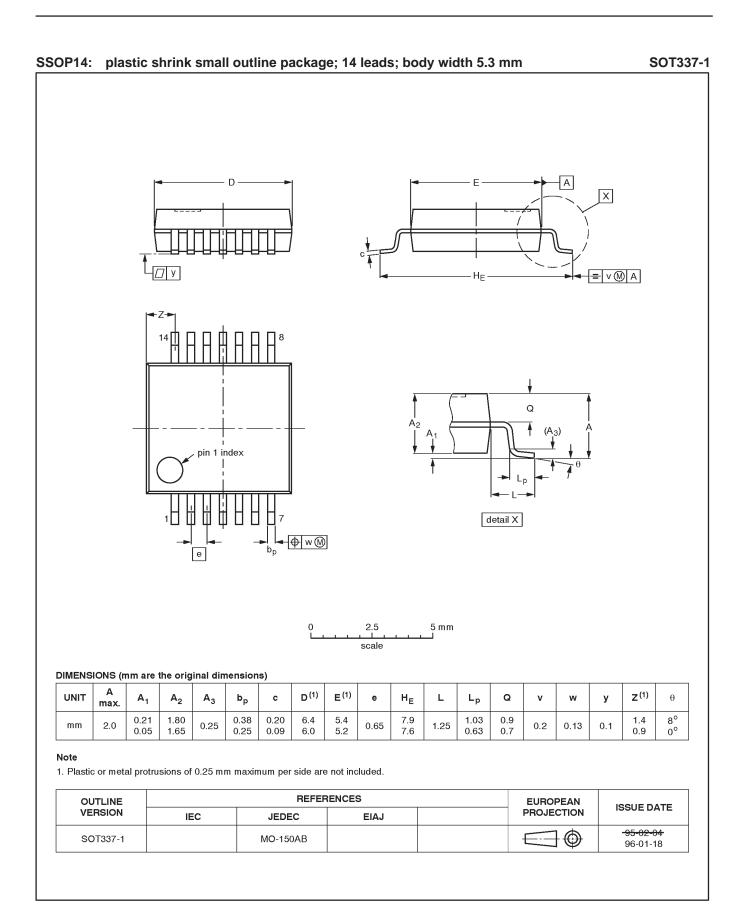
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT108-1	076E06S	MS-012AB				91-08-13 95-01-23	

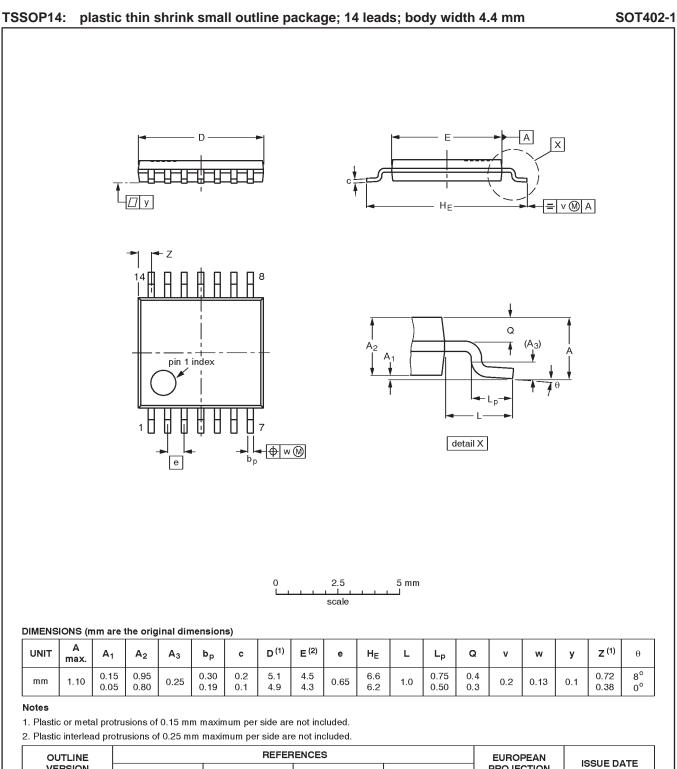
Product specification

Quad buffer/line driver (3-State)

74LV126



74LV126



74LV126

NOTES

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DEFINITIONS		
Data Sheet Identification	Product Status	Definition
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.
Preliminary Specification	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
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